

## PUBBLICAZIONI

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## VALUTAZIONE QUALITATIVA DELLA PRODUZIONE SCIENTIFICA

Due articoli sono stati inclusi tra quelli valutati dal CIVR 2001-2003 tra i prodotti presentati dal Dipartimento di Fisica con il seguente risultato:

**MAGRI R., ZUNGER A. (2002).** *Effects of interfacial atomic segregation and intermixing on the electronic properties of InAs/GaSb superlattices.* PHYSICAL REVIEW. B, CONDENSED MATTER AND MATERIALS PHYSICS. vol. 65 pp. 165302-1-165302-18 ISSN: 1098-0121 IF (2006) = 3.107  
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